
SiGe, Ge, and Related Compounds 6: Materials, Processing, and Devices

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(Invited) Waveguide Germanium PIN Photodiodes for Optical Communication Applications

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L. Vivien (University of Paris-Sud), L. Virot (University of Grenoble - Alpes, University of Paris-Sud), J. M. Hartmann (CEA, LETI, MINATEC Campus, University of Grenoble - Alpes), J. M. Fédéli (CEA, LETI, University of Grenoble - Alpes), D. Marris-Morini, E. Cassan (University of Paris-Sud), C. Baudot, F. Boeuf (STMicroelectronics)

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A. Sammak (TU Delft), M. Aminian (EPFL), L. Qi, W. B. de Boer (TU Delft), E. Charbon (EPFL, TU Delft), L. K. Nanver (TU Delft)

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Chapter 20
Strain 2

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(Invited) High Ge Content SiGe Thin Films: Growth, Properties and Integration

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*A. Y. Hikavyy, E. Rosseel, S. K. Dhayalan, L. Witters, H. Mertens, H. Bender,
P. Favia, R. Loo (IMEC)*

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*S. Yamamoto, D. Kosemura, S. N. C.M.Yusoff, T. Kijima, R. Imai, K. Takeuchi,
R. Yokogawa (Meiji University), K. Usuda (National Institute of Advanced Industrial
Science and Technology (AIST)), A. Ogura (Meiji University)*

Chapter 21

GeSn Session 3: GeSn Devices and Characterization

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*X. Gong, Y. Yang, P. Guo, W. Wang, R. Cheng, L. Wang, E. S. Tok, Y. C. Yeo
(National University of Singapore)*

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vzw), G. Simpson, G. Bast, K. Swaminathan (KLA-Tencor)*

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O. Richard (imec), H. Bender (IMEC), B. Douhard (imec vzw), W. Vandervorst
(IMEC)*

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